

RB520-30BP

Silicon Epitaxial Planar Schottky Barrier Diode

Features

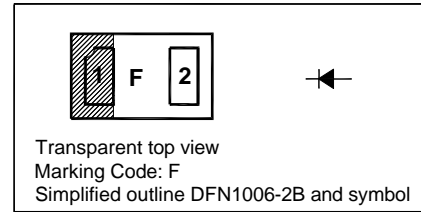
- Ultra Small mold type
- Low I_R
- High reliability

Applications

- Low current rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average rectified forward current	$I_{F(AV)}$	100	mA
Peak Forward Surge Current (8.3 ms)	I_{FSM}	500	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

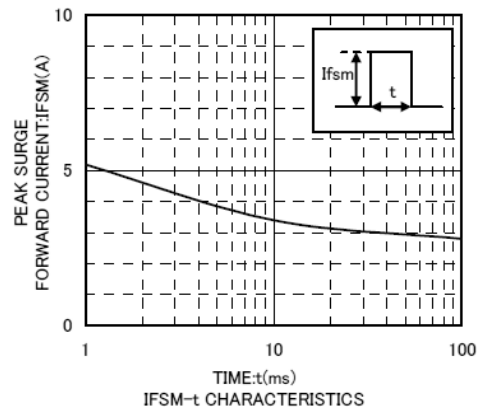
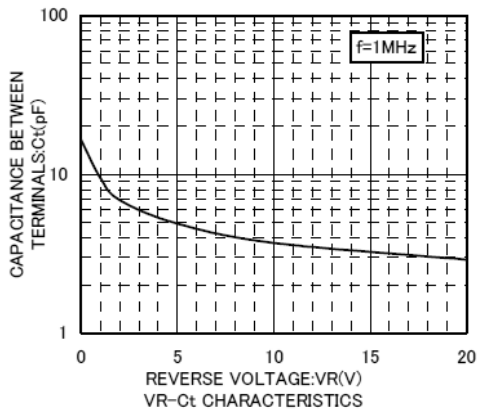
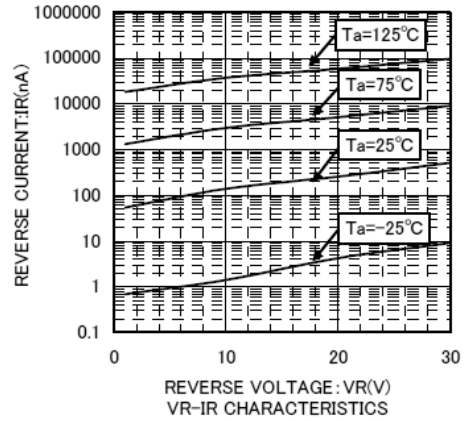
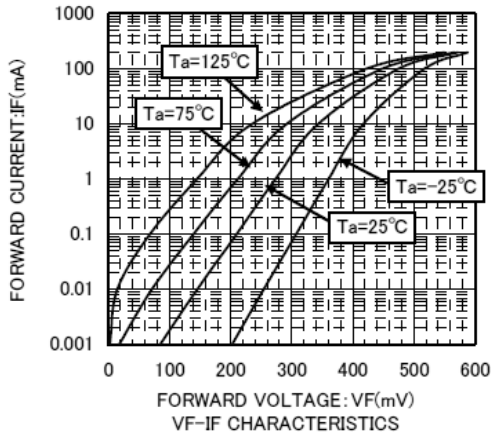
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10 \text{ mA}$	V_F	0.45	V
Reverse Current at $V_R = 10 \text{ V}$	I_R	0.5	μA

TOP DYNAMIC



Dated: 11/11/2015 Rev: 03

RB520-30BP



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ISO14001 : 2004 Certificate No. 121505007
 ISO 9001 : 2008 Certificate No. 50114012
 OHSAS 18001 : 2007 Certificate No. 05131506006
 IECQ QC 080000 Certificate No. ECG1403014.002

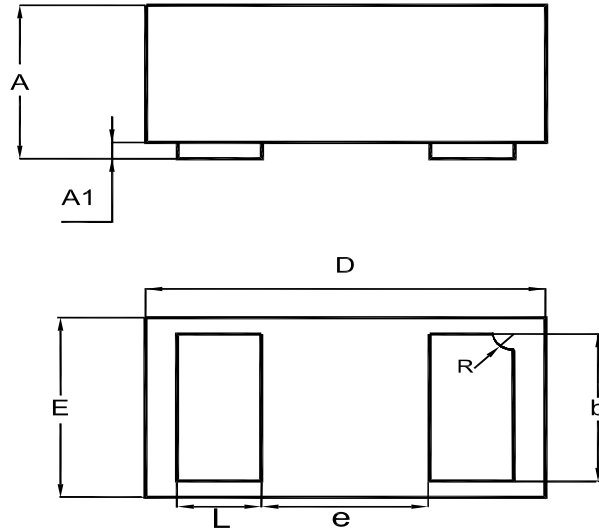
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PACKAGE OUTLINE

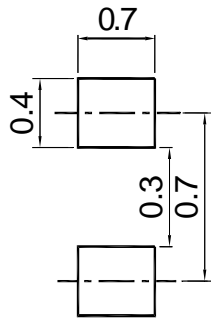
Plastic surface mounted package; 2 leads

DFN1006-2B



UNIT	A	A1	b	D	E	e	L	R
mm	0.40	0.05	0.55	1.05	0.65	0.4	0.3	0.15
	0.36	0	0.45	0.95	0.55	0.4	0.2	0.05

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN1006-2B	8	4 ± 0.1	0.157 ± 0.004	178	7	5,000

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